

Title (en)

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE INCLUDING A MASTER SLICE AND METHOD OF MAKING THE SAME

Publication

EP 0023818 A3 19821020 (EN)

Application

EP 80302606 A 19800730

Priority

JP 9762379 A 19790731

Abstract (en)

[origin: US4791474A] A semiconductor integrated circuit device includes basic semiconductor elements arranged regularly in lines and rows and located at intersecting points of the lines and rows and wiring conductor layers arranged among the basic semiconductor elements regularly in lines and rows. In this semiconductor integrated circuit device, according to a desired logic operation, wiring conductor layers are cut or contact holes are formed on the wiring conductor layers to form wiring metal layers and connect the basic semiconductor elements to one another, so that an integrated circuit chip capable of performing the desired logic operation is obtained.

IPC 1-7

H01L 23/52

IPC 8 full level

H01L 21/82 (2006.01); **H01L 21/8238** (2006.01); **H01L 23/525** (2006.01); **H01L 23/535** (2006.01); **H01L 27/092** (2006.01); **H01L 27/118** (2006.01); **H01L 27/12** (2006.01); **H01L 29/78** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP US)

H01L 23/525 (2013.01 - EP US); **H01L 23/535** (2013.01 - EP US); **H01L 27/11807** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

Citation (search report)

- [X] FR 2374817 A1 19780713 - NIPPON TELEGRAPH & TELEPHONE [JP]
- [A] US 3936812 A 19760203 - COX DENNIS T, et al
- [A] SIEMENS RESEARCH AND DEVELOPMENT REPORTS, vol. 5, no. 6, 1976, pages 344-349, Berlin (DE); E. GONAUSER et al.: "A master slice design concept based on master cells in ESFI-SOS-CMOS technology".

Cited by

FR2607966A1; EP0166027A3; FR2718288A1; DE3927143A1; DE3427285A1; US4766475A

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DE FR GB NL

DOCDB simple family (publication)

US 4791474 A 19881213; DE 3071550 D1 19860522; EP 0023818 A2 19810211; EP 0023818 A3 19821020; EP 0023818 B1 19860416; JP S5621364 A 19810227; JP S5843905 B2 19830929

DOCDB simple family (application)

US 13132387 A 19871208; DE 3071550 T 19800730; EP 80302606 A 19800730; JP 9762379 A 19790731